

Fig.1

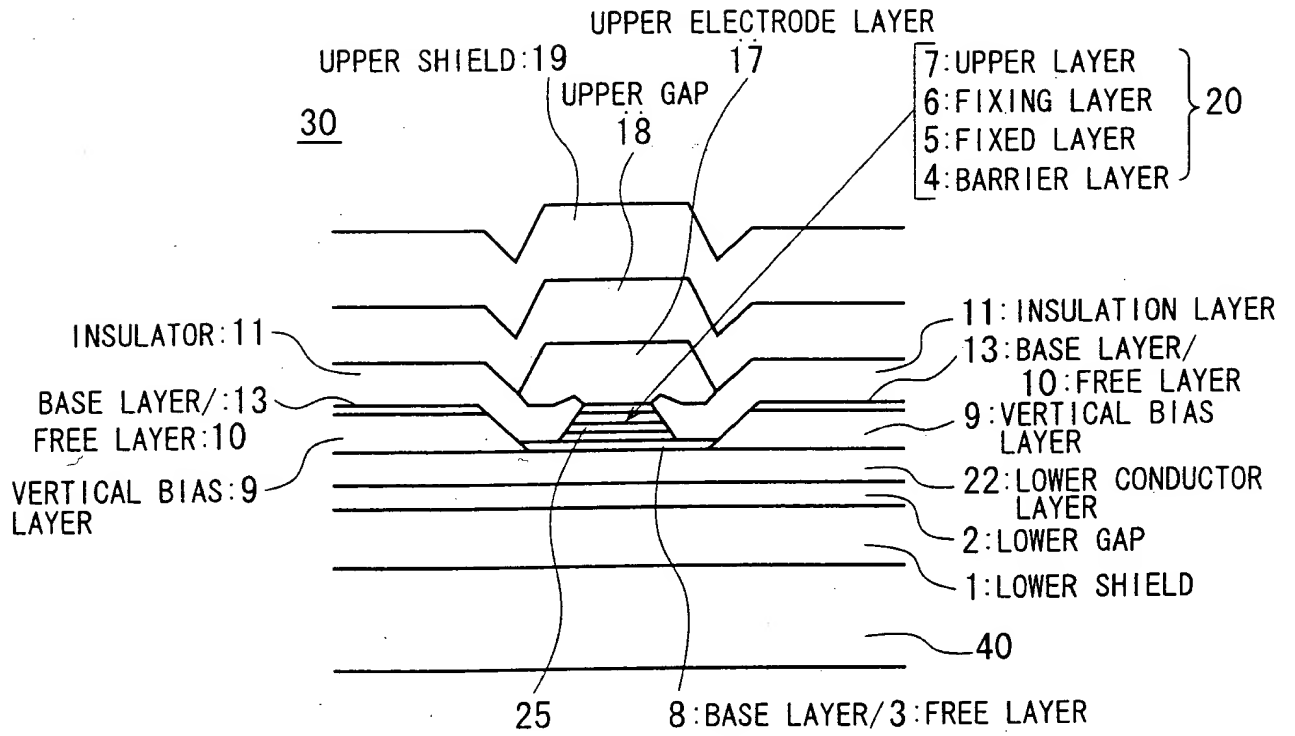


Fig.2

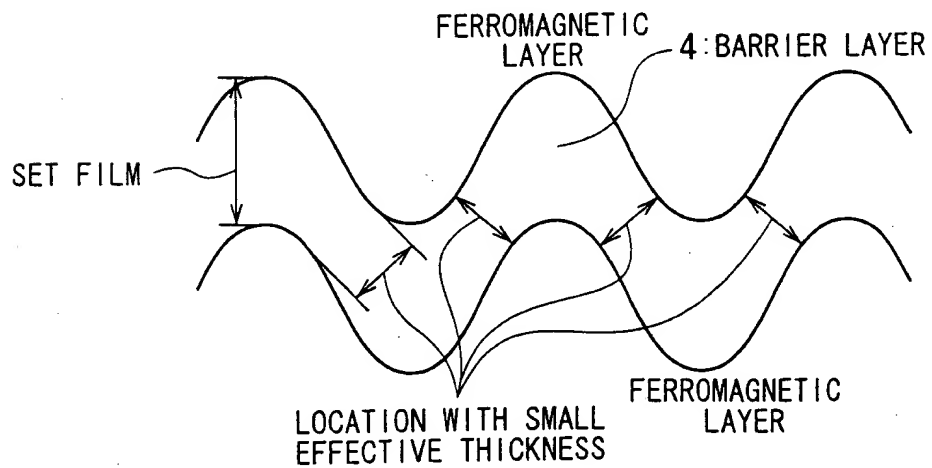


Fig.3

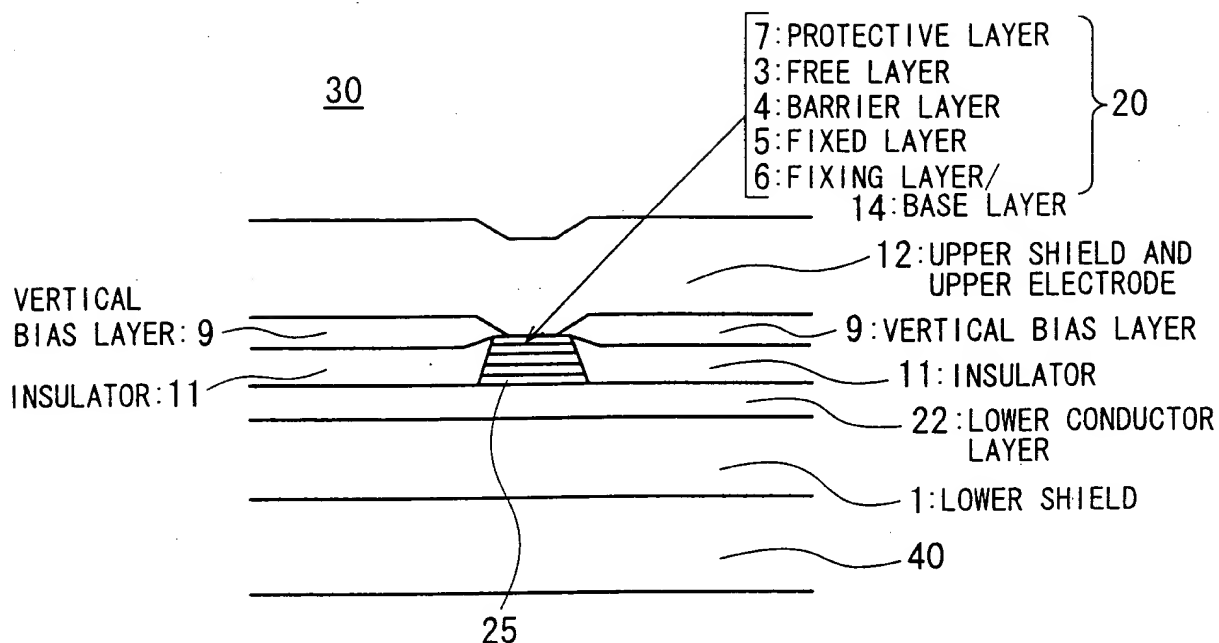
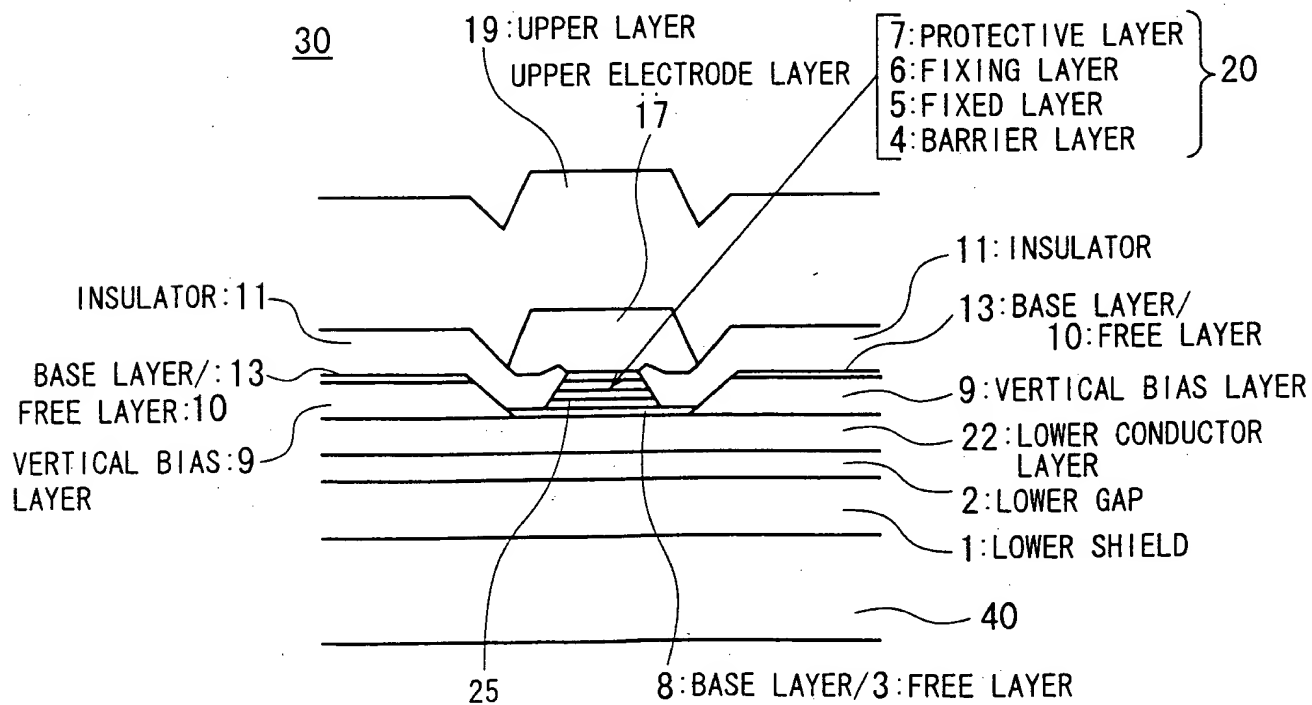


Fig.4



UPPER ELECTRODE LAYER

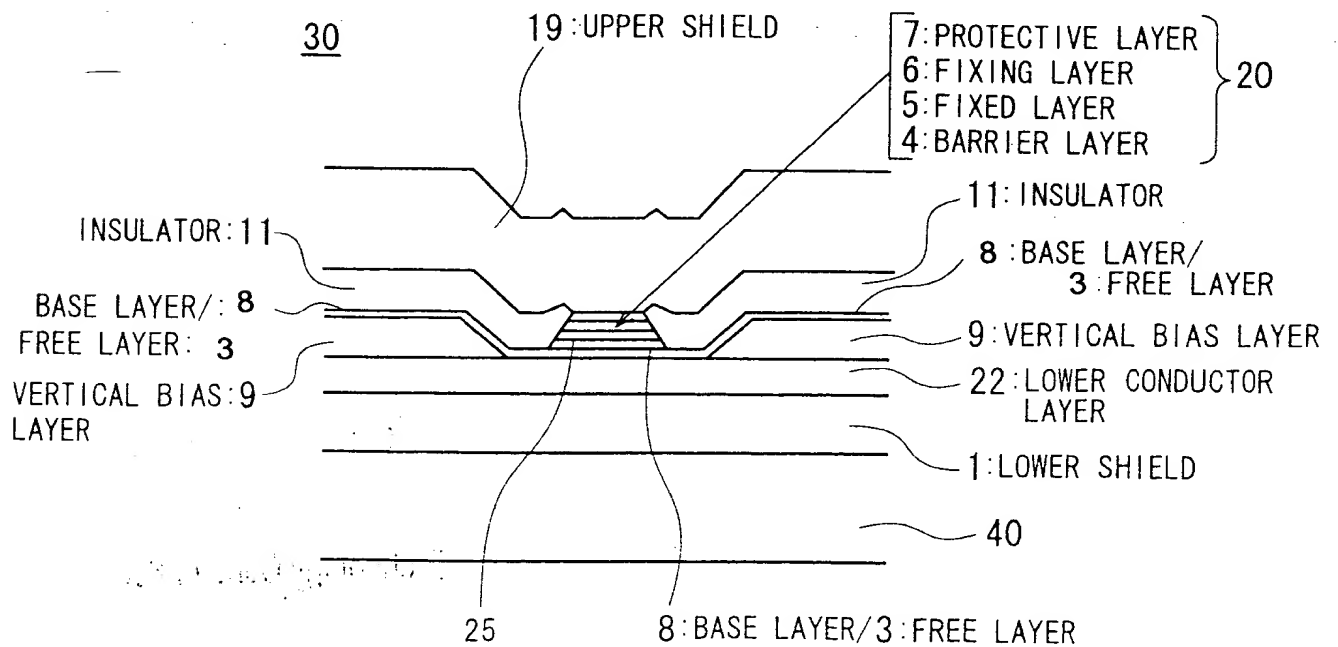


Fig.7

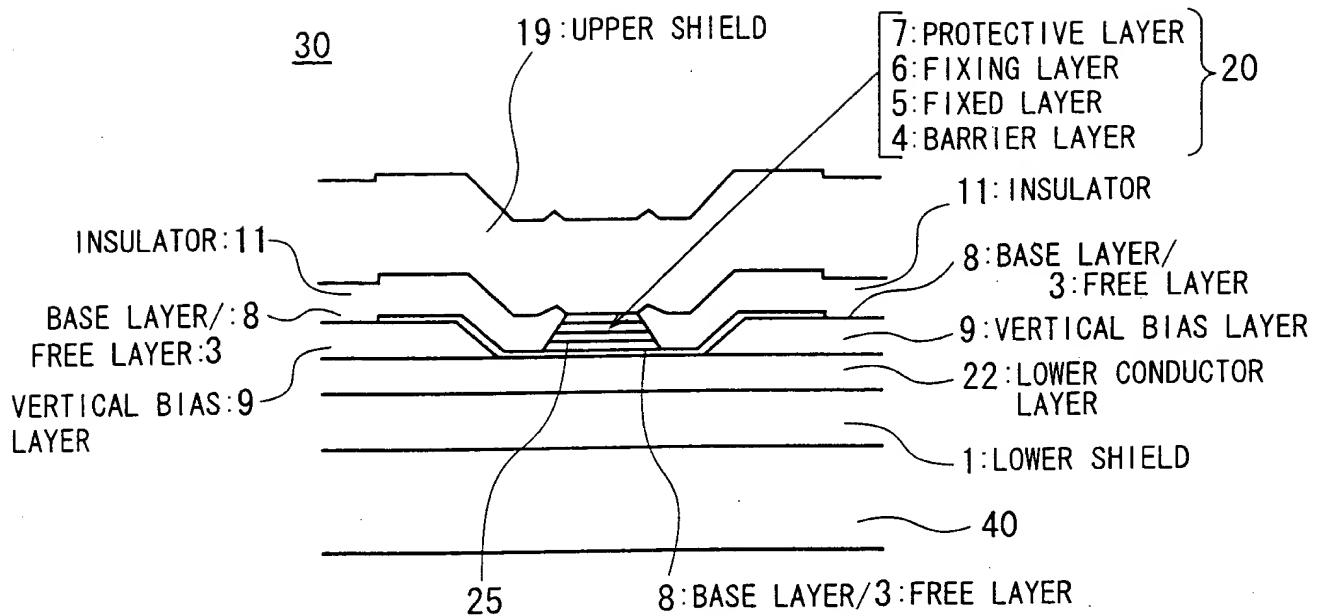


Fig.8

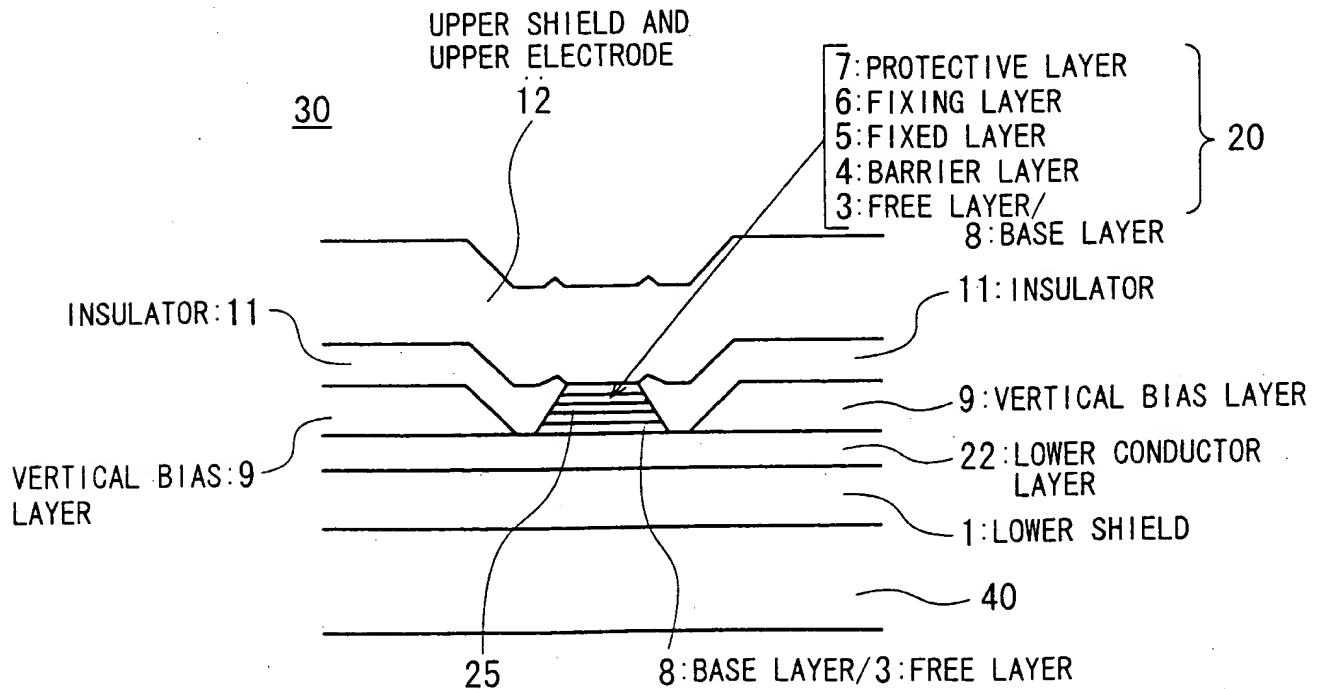


Fig.9

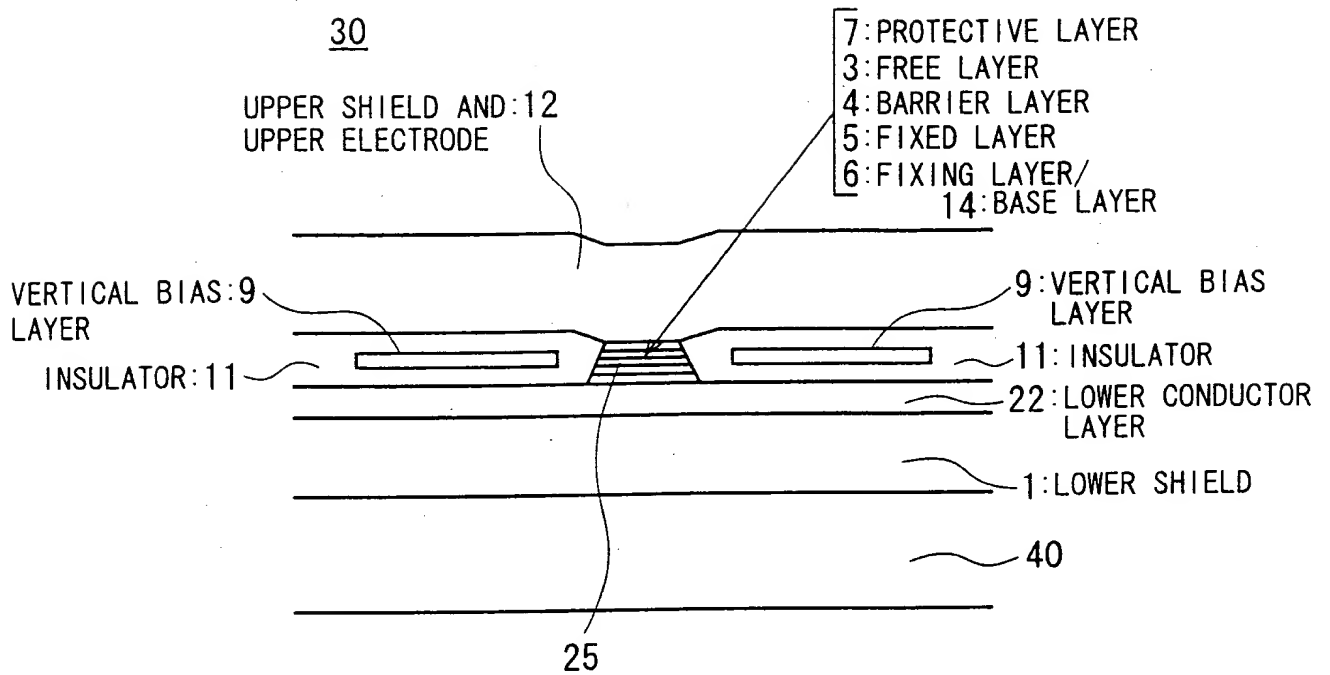
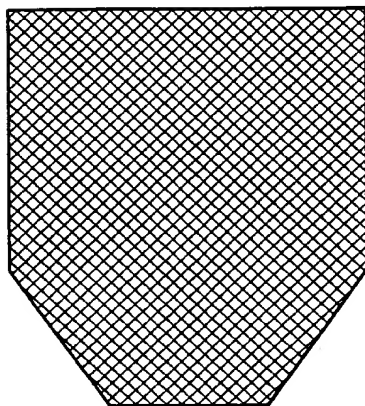
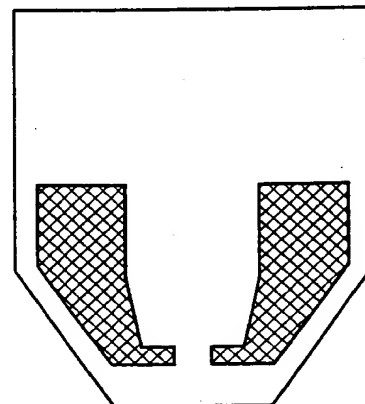


Fig.10(A)



LOWER SHIELD AND LOWER CONDUCTOR LAYER FORMED AS FILMS AND PATTERNED (PR FORMATION → PR REMOVAL)

Fig.10(B)



VERTICAL BIAS LAYER BASE LAYER/VERTICAL BIAS LAYER FILM FORMATION AND PATTERNING (PR FORMATION → PR REMOVAL)

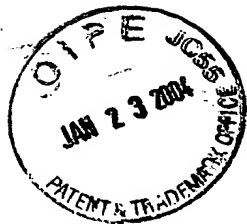
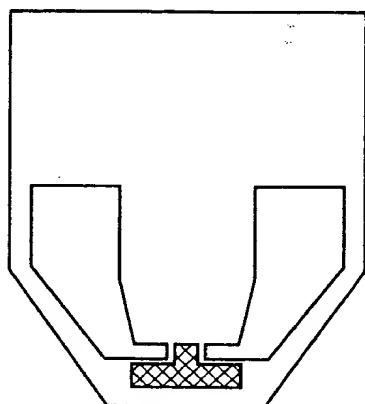
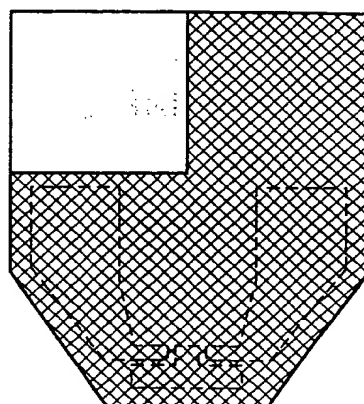


Fig.11(A)



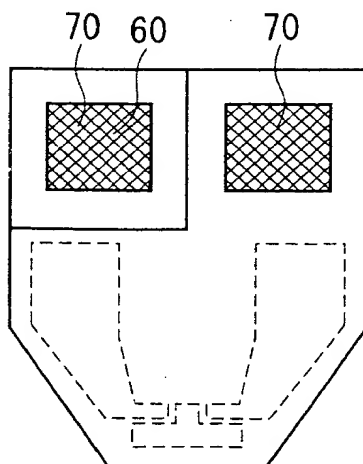
MAGNETORESISTIVE EFFECT FILM →
 PR FORMATION → MILLING →
 INSULATION FILM FORMATION → LIFT-OFF

Fig.11(B)



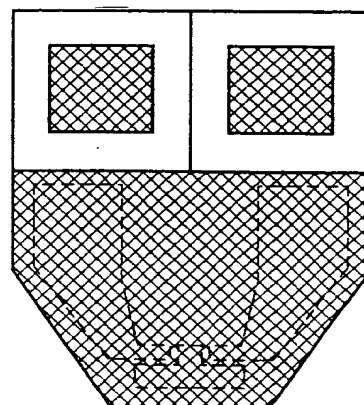
UPPER SHIELD FORMATION → PR FORMATION
 → PATTERNING → PR REMOVAL

Fig.12(A)



LOWER ELECTRODE HOLE FORMATION,
 ELECTRODE TERMINAL FORMATION

Fig.12(B)



RECORDING HEAD FORMATION

Fig.13

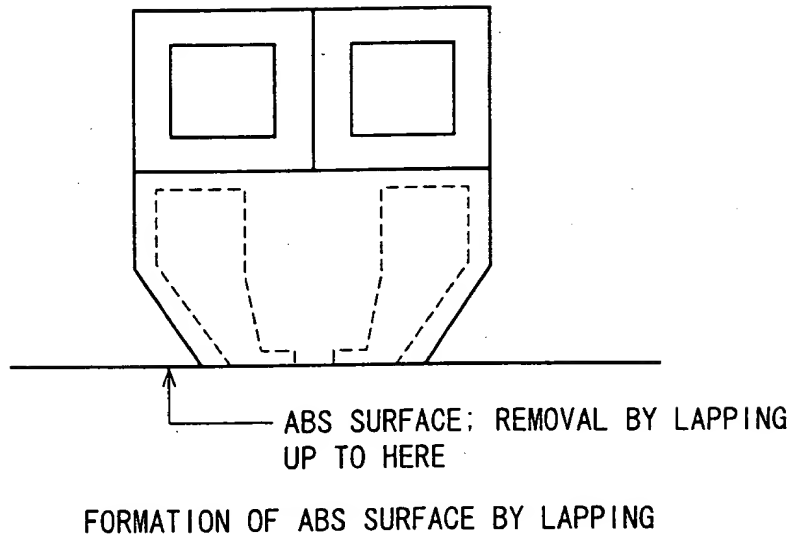


Fig.14

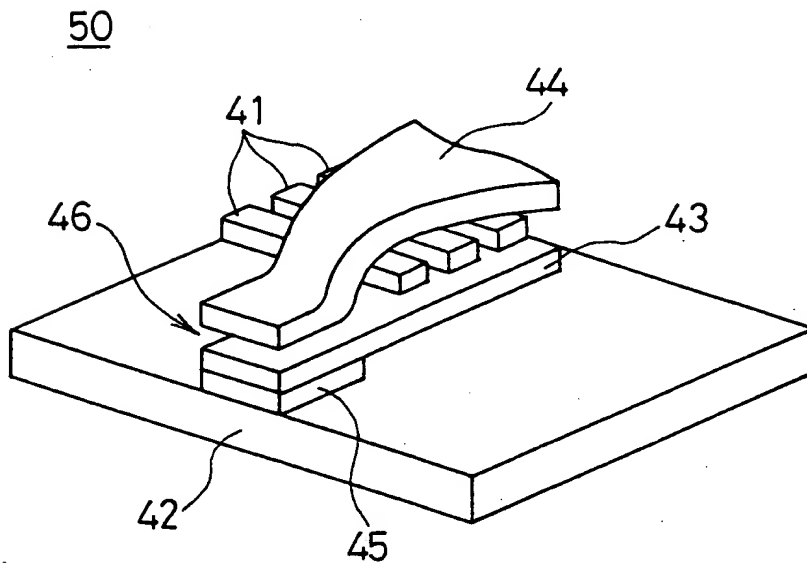


Fig.15

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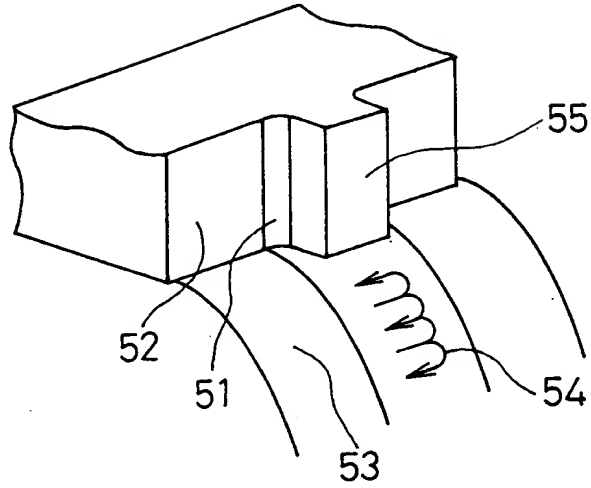
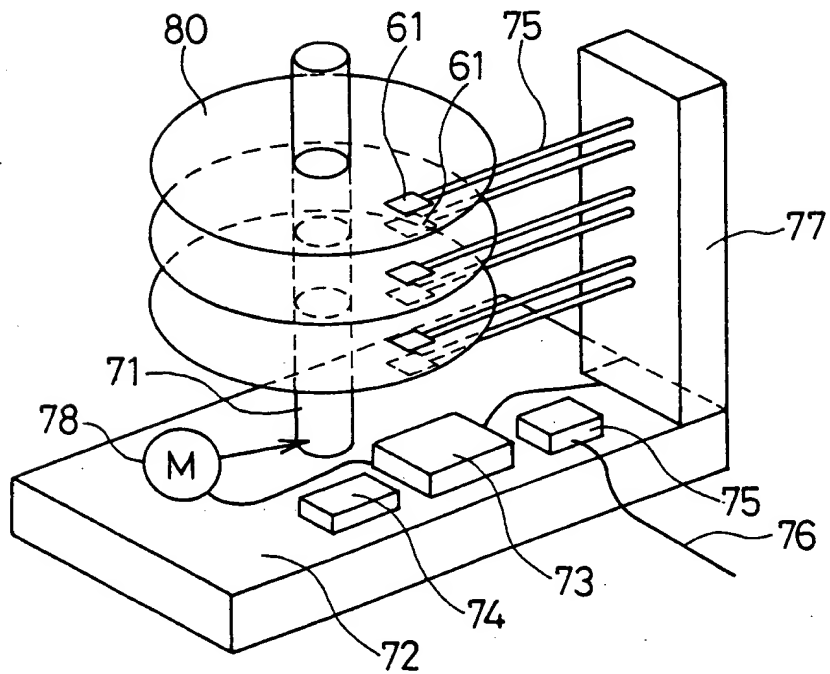


Fig.16



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